Diode Semiconductor Korea MURS140--- MURS160

SURFACE MOUNT RECTIFIERS

VOLTAGE RANGE: 400 --- 600 V

CURRENT: 1.0 A

FEATURES

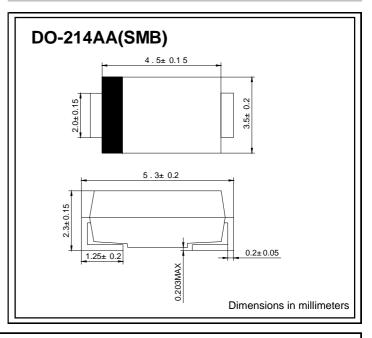
- ♦ Low cost
- ♦ Low leakage
- Low forward voltage drop
- High current capability
- Easily cleaned with Alcohol, Isopropanol and similar solvents
- ♦ The plastic material carries U/L recognition 94V-0

MECHANICAL DATA

MIL-STD-202, Method 208

♦ Polarity: Color band denotes cathode ♦ Weight: 0.003 ounces, 0.093 grams

Mounting position: Any



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load. For capacitive load, derate by 20%.

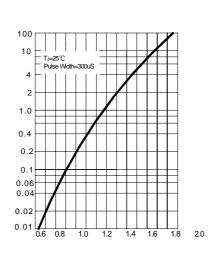
		MURS140	MURS160	UNITS
Device marking code		MG	MJ	
Maximum recurrent peak reverse voltage	V_{RRM}	400	600	V
Maximum RMS voltage	V_{RMS}	280	420	V
Maximum DC blocking voltage	V_{DC}	400	600	V
Maximum average forward rectified current @T∟=110 °C	I _{F(AV)}	1.0		А
Peak forward surge current 8.3ms single half-sine-wave superimposed on rated load $@T_J=125$ $^{\circ}C$	I _{FSM}	35		А
Typical reverse recovery time (Note1)	t _{rr}	50		ns
Maximum reverse current $@T_A = 25 \degree C$ at rated DC blocking voltage $@T_A = 125 \degree C$	I _R	5.0 150		μА
Maximum instantaneous forw ard voltage at 1.0 A	VF	1.25		V
Typical thermal resistance (Note2)	$R_{\theta JL}$	13		°C/W
Operating junction temperature range	TJ	- 55 + 150		$^{\circ}$
Storage temperature range	T _{STG}	- 55 + 150		$^{\circ}$

NOTE: 1. Measured with I_F =0.5A, I_R =1A, I_{rr} =0.25A.

www.diode.kr 2. Junction to ambient.

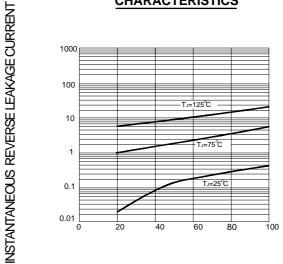
FIG.1 - TYPICAL FORWARD CHARACTERISTIC

INSTANTANEOUS FORWARD CURRENT AMPERES



INSTANTANEOUS FORWARD VOLTAGE, VOLTS

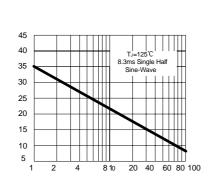
FIG.2 -- TYPICAL REVERSE LEAKAGE CHARACTERISTICS



PERCENT OF RATED PEAK REVERSE VOLTAGE (%)

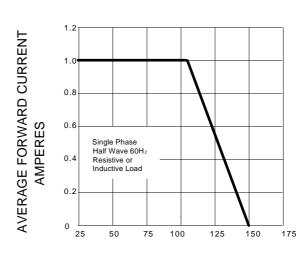
FIG.3 - PEAK FORWARD SURGE CURRENT

PEAK FORWARD SURGE CURRENT AMPERES



NUMBER OF CYCLES AT 60Hz

FIG.4 - FORWARD DERATING CURVE



LEAD TEMPERATURE, °C